1. General description

PNP/PNP general-purpose double transistor in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: BC846BSH-Q NPN/PNP complement: BC846BPNH-Q

2. Features and benefits

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and board space
- No mutual interference between the transistors
- High-temperature applications up to 175 °C
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

· General-purpose switching and amplification

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
V _{CEO}	collector-emitter voltage	open base	-	-	-65	V
I _C	collector current		-	-	-100	mA
h _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -2 mA; T_{amb} = 25 °C	200	300	450	



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	□6 □5 □4	C1 B2 E2
2	B1	base TR1		
3	C2	collector TR2		(TR1) TR2)
4	E2	emitter TR2	H ₁ H ₂ H ₃	
5	B2	base TR2	TSSOP6 (SOT363)	I I I E1 B1 C2
6	C1	collector TR1		sym138

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BC856BSH-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
BC856BSH-Q	2E%

^{[1] % =} placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

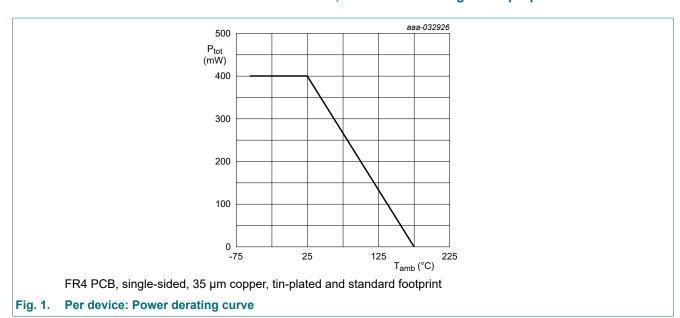
Symbol	Parameter	Conditions		Min	Max	Unit
Per transistor						
V _{CBO}	collector-base voltage	open emitter		-	-80	V
V _{CEO}	collector-emitter voltage	open base		-	-65	V
V _{EBO}	emitter-base voltage	open collector		-	-7	V
I _C	collector current			-	-100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-200	mA
I _{BM}	peak base current			-	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	270	mW
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	400	mW
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.

BC856BSH-Q

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65 V, 100 mA PNP/PNP general-purpose double transistor

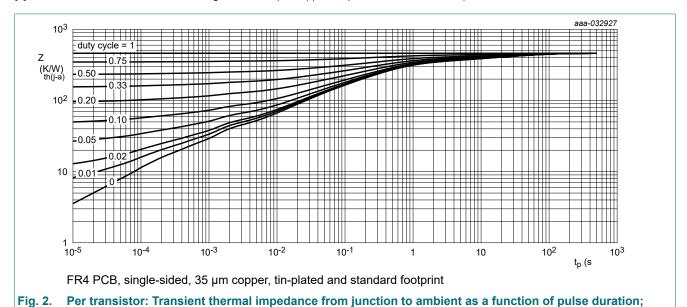


9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions			Min	Тур	Max	Unit
Per transiste	or		,					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]]	-	-	556	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point				-	-	170	K/W
Per device								
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]]	-	-	375	K/W

[1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.



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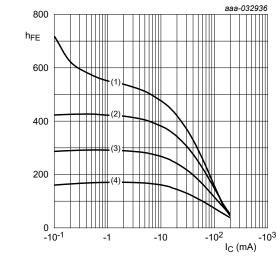
typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = -100 \mu A; I_E = 0 A; T_{amb} = 25 °C$		-80	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = -2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-65	-	-	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_C = 0 \text{ A}; I_E = -100 \mu\text{A}; T_{amb} = 25 \text{ °C}$		-7	-	-	V
I _{CBO}	collector-base cut-off	V _{CB} = -30 V; I _E = 0 A; T _{amb} = 25 °C		-	-	-15	nA
	current	V _{CB} = -30 V; I _E = 0 A; T _j = 150 °C		-	-	-5	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = -7 V; I _C = 0 A; T _{amb} = 25 °C		-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -2 mA; T_{amb} = 25 °C		200	300	450	
V _{CEsat}	collector-emitter saturation voltage	I_C = -10 mA; I_B = -0.5 mA; T_{amb} = 25 °C		-	-50	-100	mV
		I_C = -100 mA; I_B = -5 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C		-	-200	-300	mV
V _{BEsat}		I_C = -10 mA; I_B = -0.5 mA; T_{amb} = 25 °C	[1]	-	-750	-850	mV
	voltage	I_C = -100 mA; I_B = -5 mA; T_{amb} = 25 °C		-	-875	-	mV
V_{BE}	base-emitter voltage	V_{CE} = -5 V; I_{C} = -2 mA; T_{amb} = 25 °C	[2]	-600	-655	-700	mV
		V _{CE} = -5 V; I _C = -10 mA; T _{amb} = 25 °C	[2]	-	-705	-770	mV
C _c	collector capacitance	V_{CB} = -10 V; I_E = 0 A; i_e = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	1.8	-	pF
C _e	emitter capacitance	V_{EB} = -0.5 V; I_{C} = 0 A; i_{c} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	8.5	-	pF
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C		100	-	-	MHz
NF	noise figure	V_{CE} = -5 V; I_{C} = -0.2 mA; R_{S} = 2 k Ω ; f = 10 Hz to 15.7 kHz; T_{amb} = 25 °C		-	1.7	-	dB
		V_{CE} = -5 V; I_{C} = -0.2 mA; R_{S} = 2 k Ω ; f = 1 kHz; B = 200 Hz; T_{amb} = 25 °C		-	3.3	-	dB

 $[\]rm V_{BEsat}$ decreases by about 1.7 mV/K with increasing temperature. $\rm V_{BE}$ decreases by about 2 mV/K with increasing temperature.



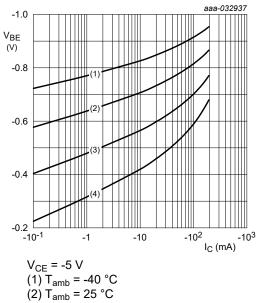
 V_{CE} = -5 V

 $(1) T_{amb} = 175 °C$

(2) $T_{amb} = 100 \, ^{\circ}C$

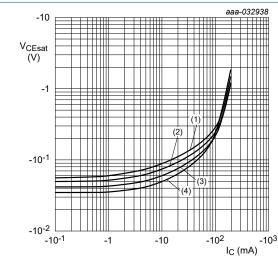
(3) $T_{amb} = 25 ^{\circ}C$ (4) $T_{amb} = -40 ^{\circ}C$

DC current gain as a function of collector Fig. 3. current; typical values



(3) T_{amb} = 100 °C (4) T_{amb} = 175 °C

Base-emitter voltage as a function of collector Fig. 4. current; typical value



 $I_{\rm C}/I_{\rm B} = 20$

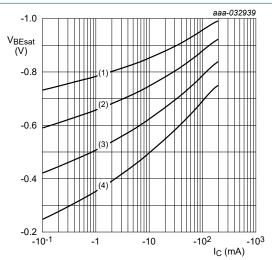
 $(1) T_{amb} = 175 °C$

(2) T_{amb} = 100 °C

(3) $T_{amb} = 25 \, ^{\circ}C$

(4) $T_{amb} = -40 \, ^{\circ}C$

Fig. 5. Collector-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$

(1) T_{amb} = -40 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

(4) $T_{amb} = 175 \, ^{\circ}C$

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values

65 V, 100 mA PNP/PNP general-purpose double transistor

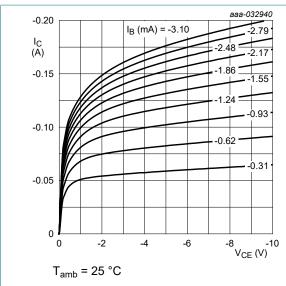
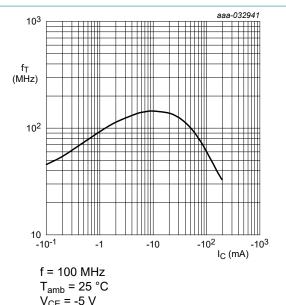


Fig. 7. Collector current as a function of collectoremitter voltage; typical values



 $V_{CE} = -5 V$

Fig. 8. Transition frequency as a function of collector current; typical values

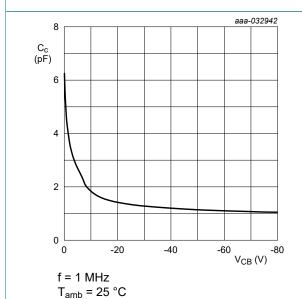
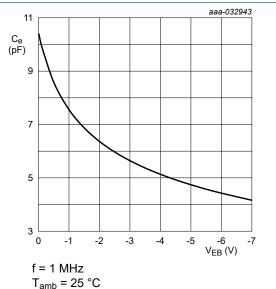


Fig. 9. base voltage; typical values



Collector capacitance as a function of collector- Fig. 10. Emitter capacitance as a function of emitterbase voltage; typical values

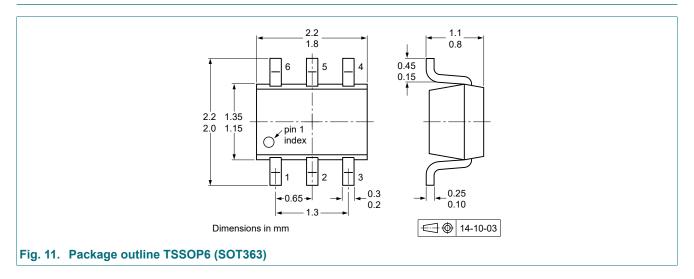
11. Test information

Quality information

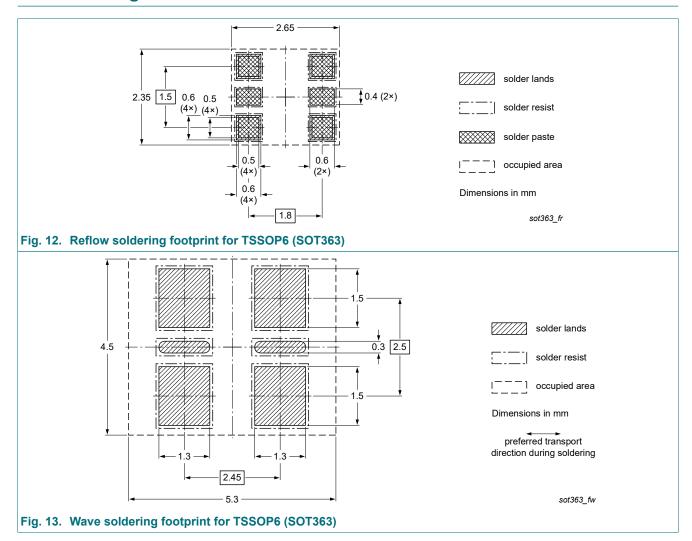
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

65 V, 100 mA PNP/PNP general-purpose double transistor

12. Package outline



13. Soldering



65 V, 100 mA PNP/PNP general-purpose double transistor

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BC856BSH-Q v.1	20210506	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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